MMBTA55 / MMBTA56

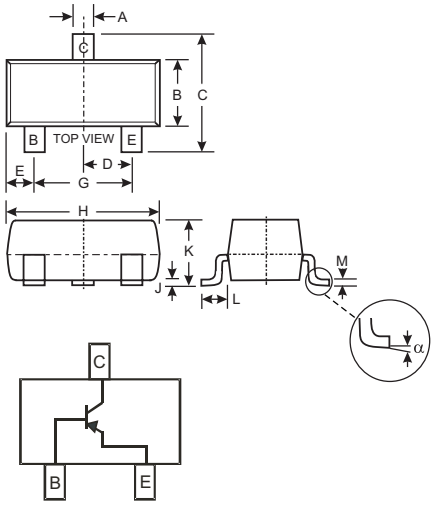
PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (MMBTA05 / MMBTA06)
- Ideal for Medium Power Amplification and Switching
- **Lead Free/RoHS Compliant (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- MMBTA55 Marking (See Page 2): K2H
- MMBTA56 Marking (See Page 2): K2G
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	**Min**	**Max**
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	MMBTA55	MMBTA56	Unit
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	V
Emitter-Base Voltage	V_{EBO}	-4.0		V
Collector Current - Continuous (Note 1)	I_C	-500		mA
Power Dissipation (Note 1)	P_d	300		mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417		°C/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150		°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Collector-Base Breakdown Voltage	MMBTA55 MMBTA56	$V_{(BR)CBO}$	-60 -80	—	V	I_C = -100μA, I_E = 0
Collector-Emitter Breakdown Voltage	MMBTA55 MMBTA56	$V_{(BR)CEO}$	-60 -80	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-4.0	—	V	I_E = -100μA, I_C = 0
Collector Cutoff Current	MMBTA55 MMBTA56	I_{CBO}	—	-100	nA	V_{CB} = -60V, I_E = 0 V_{CB} = -80V, I_E = 0
Collector Cutoff Current	MMBTA55 MMBTA56	I_{CEX}	—	-100	nA	V_{CE} = -60V, I_{BO} = 0V V_{CE} = -80V, I_{BO} = 0V
ON CHARACTERISTICS (Note 2)						
DC Current Gain		h_{FE}	100	—	—	I_C = -10mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	—	-0.25	V	I_C = -100mA, I_B = -10mA
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$	—	-1.2	V	I_C = -100mA, V_{CE} = -1.0V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product		f_T	50	—	MHz	V_{CE} = -1.0V, I_C = -100mA, f = 100MHz

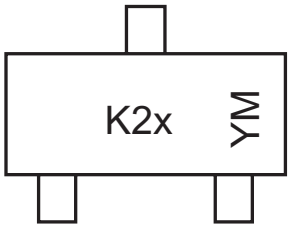
Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. Short duration test pulse used to minimize self-heating effect.
3. No purposefully added lead.

Ordering Information (Note 4)

Device	Packaging	Shipping
MMBTA55-7-F MMBTA56-7-F	SOT-23	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K2x = Product Type Marking Code, ex: K2H = MMBTA55
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

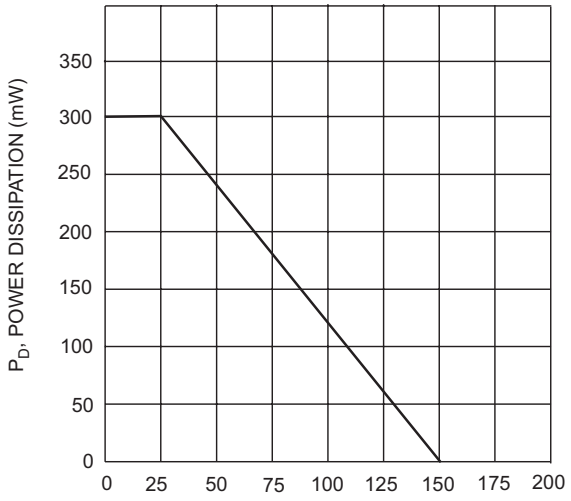


Fig. 1, Max Power Dissipation vs Ambient Temperature

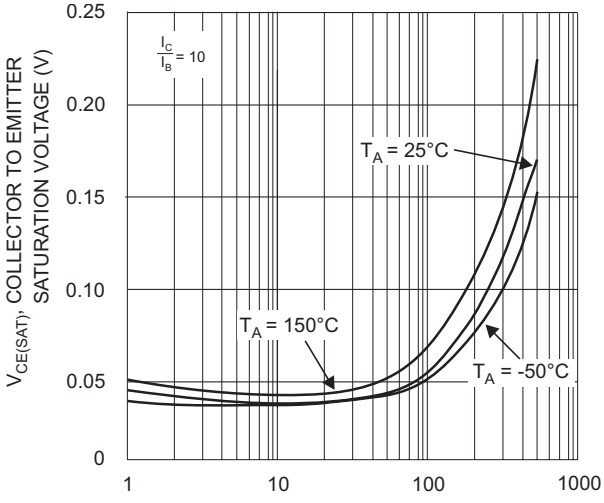


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

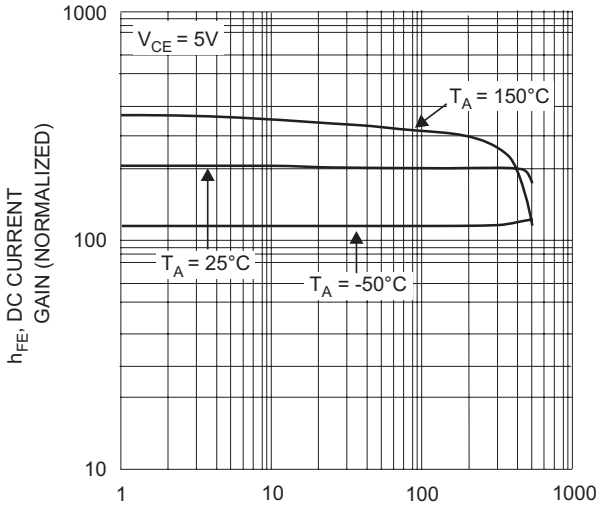


Fig. 3, DC Current Gain vs Collector Current

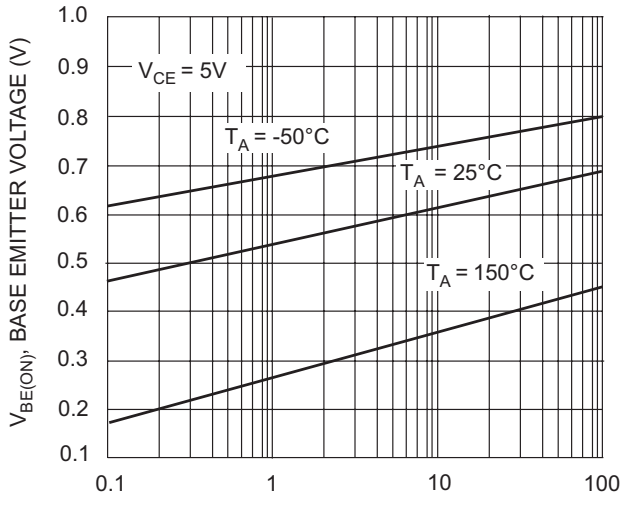


Fig. 4 Base Emitter Voltage vs. Collector Current

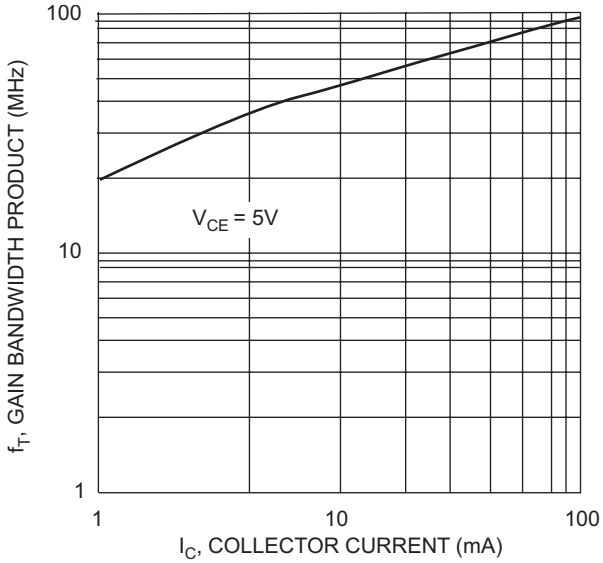


Fig. 5 Gain Bandwidth Product vs. Collector Current